40 Watt Peak Power Zener Transient Voltage Suppressors

SC-70 Dual Common Anode Zeners for ESD Protection

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Features

- SC-70 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range
- Standard Zener Breakdown Voltage Range 27 V
- Peak Power 40 W @ 1.0 ms (Unidirectional), per Figure 5 Waveform
- ESD Rating:
 - Class 3B (>16 kV) per the Human Body Model
 Class C (>400 V) per the Machine Model
- Low Leakage < 5.0 μA
- Flammability Rating UL 94 V–0
- This is a Pb–Free Device

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic case FINISH: Corrosion resistant finish, easily solderable MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

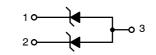
Package designed for optimal automated board assembly Small package size for high density applications Available in 8 mm Tape and Reel

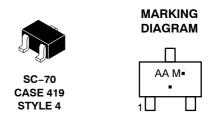
Use the Device Number to order the 7 inch/3,000 unit reel. Replace the "T1" with "T3" in the Device Number to order the 13 inch/10,000 unit reel.



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AA = Specific Device Code

- M = Date Code
- = Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBZ27VAWT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ $T_L \le 25^{\circ}C$	P _{pk}	40	W
Total Power Dissipation on FR–5 Board (Note 2) @ T _A = 25°C Derate above 25°C	PD	200 1.6	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	618	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	– 55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Non-repetitive current pulse per Figure 5 and derate above $T_A = 25^{\circ}C$ per Figure 6.

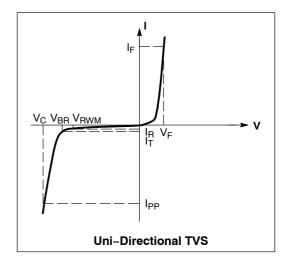
2. FR-5 = 1.0 x 0.75 x 0.62 in.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
V _C	Clamping Voltage @ IPP					
V _{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
V _{BR}	Breakdown Voltage @ I _T					
Ι _Τ	Test Current					
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}					
١ _F	Forward Current					
V _F	Forward Voltage @ I _F					
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}					
I _{ZK}	Reverse Current					
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}					



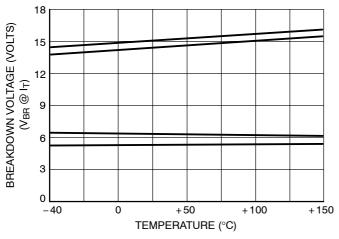
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 0.9 \text{ V Max} @ I_F = 10 \text{ mA})$

			I _R @	Breakdown Voltage			1	V _C @ I _{PP}	(Note 4)	
	Device	V _{RWM}	V _{RWM}	V _{BR} (Note 3) (V)		@ I _T	v _c	I _{PP}	ΘV _{BR}	
Device	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ27VAWT1G	AA	22	50	25.65	27	28.35	1.0	40	1.0	24.3

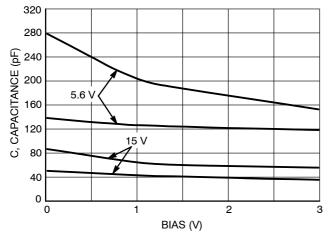
3. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C. 4. Surge current waveform per Figure 5 and derate per Figure 6

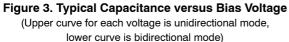
TYPICAL CHARACTERISTICS





(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)





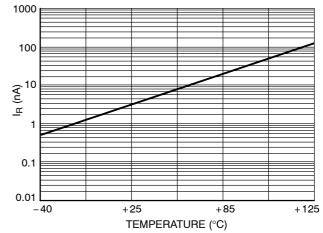


Figure 2. Typical Leakage Current versus Temperature

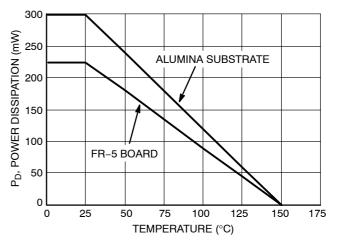
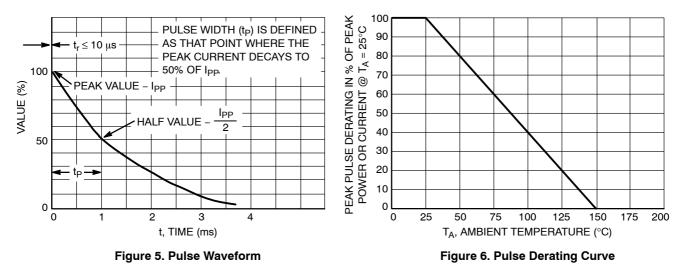


Figure 4. Steady State Power Derating Curve

TYPICAL CHARACTERISTICS



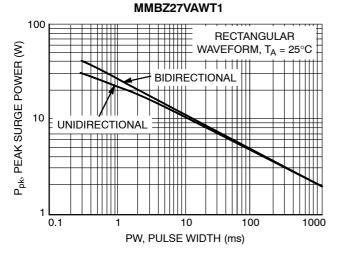


Figure 7. Maximum Non-repetitive Surge Power, P_{pk} versus PW

Power is defined as $V_{RSM} \times I_Z(pk)$ where V_{RSM} is the clamping voltage at $I_Z(pk)$.

MMBZ27VAWT1

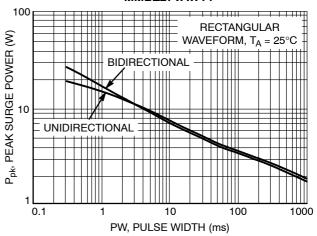
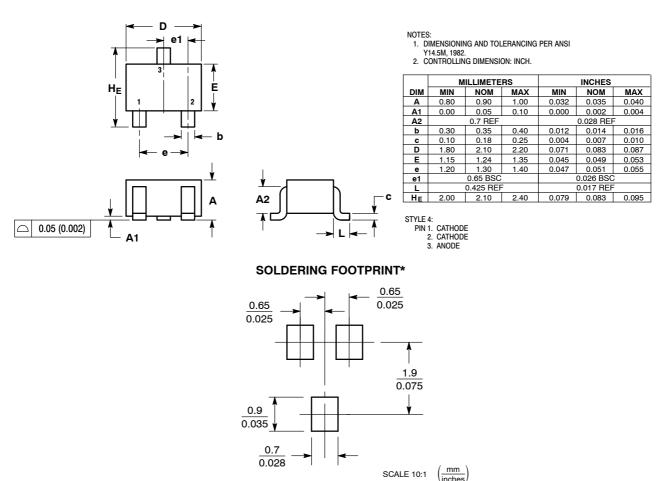


Figure 8. Maximum Non-repetitive Surge Power, P_{pk}(NOM) versus PW

Power is defined as $V_Z(NOM) \times I_Z(pk)$ where $V_Z(NOM)$ is the nominal Zener voltage measured at the low test current used for voltage classification.

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE M



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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